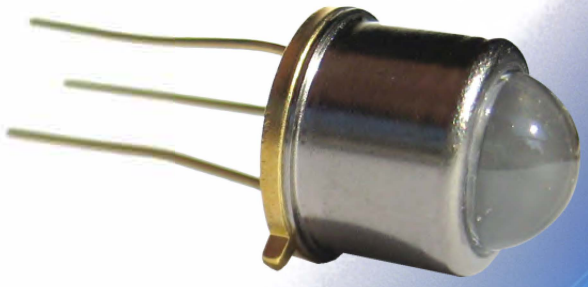
Ball Lens UV LED



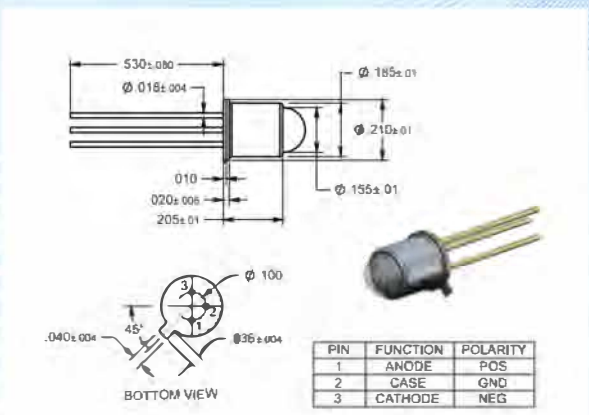
Smaller Size and Lower Cost than Traditional LEDs

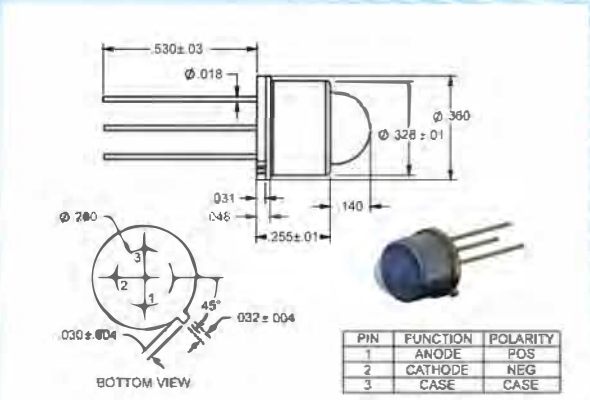
Our Deep UV LEDs are available in a wide range of wavelengths and package sizes. These devices are manufactured using AlGaN/GaN technology that enables a new generation of High Band-Gap Energy opto-electronics devices able to perform down to 240 nm.

These small UV LEDs consume significantly less power than comparable UV technologies and come in several standard configurations. The Ball Lens is ideal for applications that require a small or focused spot of UV light.

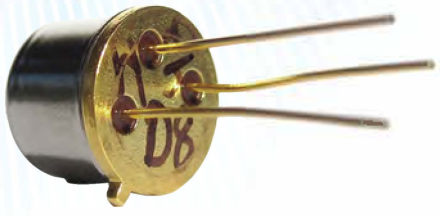
Electro-optical characteristics

Parameter	Symbol	Unit	Minimum	Typical	Maximum	Condition
Forward voltage	VF	V	5.5	7.5	9	IF=20 mA
Reverse current	IR	µA	100	VR=5V		
Output UV power	Pout	mW	0.5			IF=20 mA
Peak wavelength	λp	nm	-10 nm	specified	+10 nm	IF=20 mA
Spectrum half width	HW	nm	12	20	30	IF=20 mA





Parameter	Unit	Max rated Value	Ambient Temp
Power dissipation, DC	mW	150	25 °C
Forward current, DC	mA	30	25 °C
Pulse forward current	mA	200	25 °C
Reverse voltage	V	6	25 °C
Storage temperature		- 30 ~ + 100 °C	



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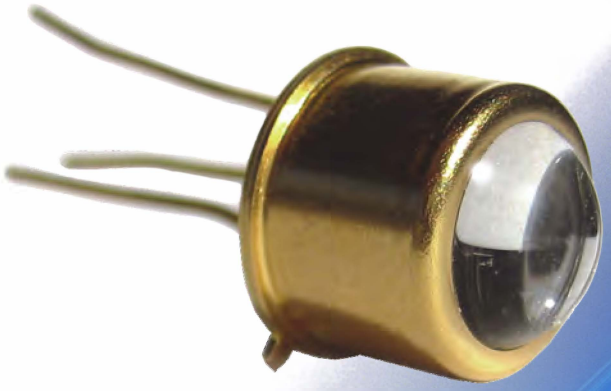
Hemispherical Lens LED



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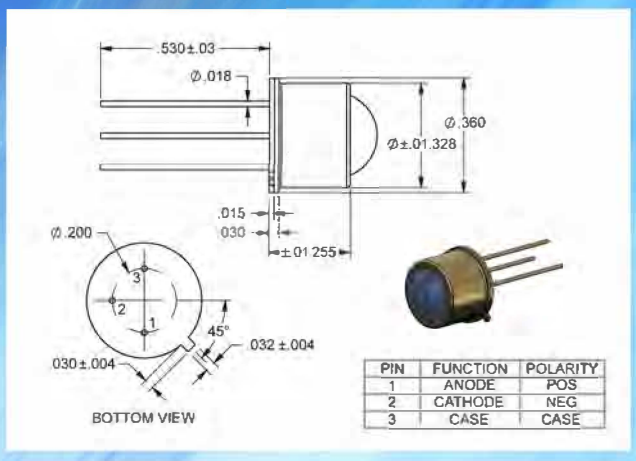
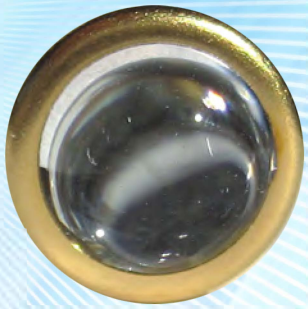
These small UV LEDs consume significantly less power than comparable UV technologies and come in several standard configurations. The Ball Lens is ideal for applications that require a small or focused spot of UV light.





Parameter	Unit	Max rated Value	Ambient Temp	Parameter
Power dissipation, DC	mW	150	25 °C	Forward voltage
Forward current, DC	mA	30	25 °C	Reverse current
Pulse forward current	mA	200	25 °C	Output UV power
	V	6	25 °C	Peak wavelength
Storage temperature		- 30 ~ + 100 °C		Spectrum half width

Electro-optical characteristics

Parameter	Symbol	Unit	Minimum	Typical	Maximum	Condition
Forward voltage	VF	V	5.5	7.5	9	IF=20mA
Reverse current	IR	μA	100	VR=5V		
Output UV power	Pout	mW	0.5			IF=20mA
Peak wavelength	λp	nm	-10 nm	specified	+10 nm	IF=20mA
Spectrum half width	HW	nm	12	20	30	IF=20mA

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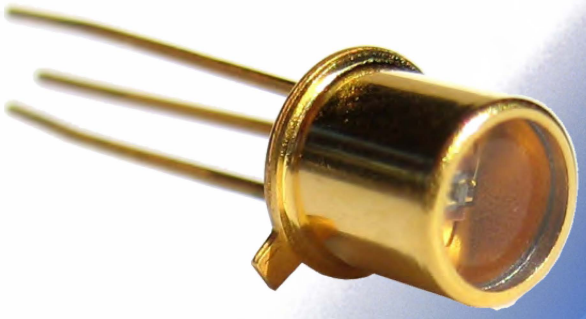
Flat Lens UV LED



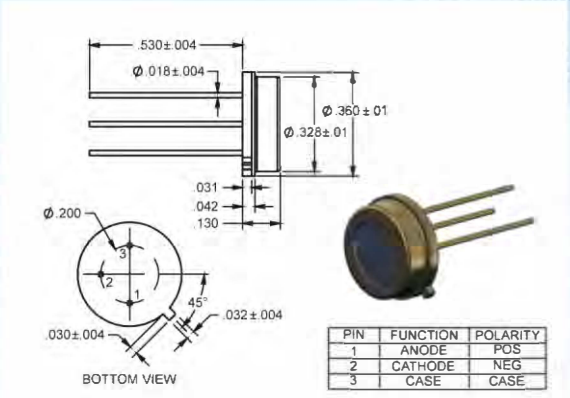
Smaller Size and Lower Cost than Traditional LEDs

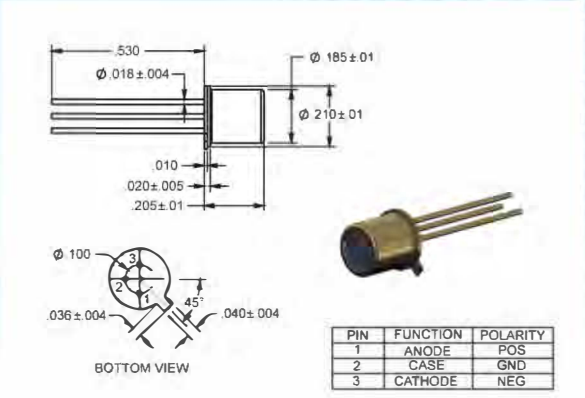
Our Deep UV LEDs are available in a wide range of wavelengths and package sizes. These devices are manufactured using AlGaN/GaN technology that enables a new generation of High Band-Gap Energy opto-electronics devices able to perform down to 240 nm.

These small UV LEDs consume significantly less power than comparable UV technologies and come in several standard configurations. The Flat Lens is ideal for applications that require a more widely spread spot of UV light.

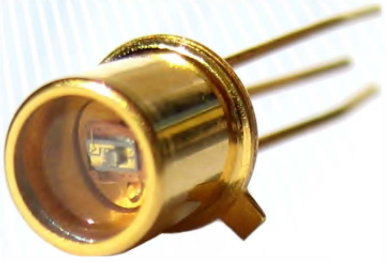
Electro-optical characteristics

Parameter	Symbol	Unit	Minimum	Typical	Maximum	Condition
Forward voltage	VF	V	5.5	7.5	9	IF=20 mA
Reverse current	IR	µA	100	VR=5V		
Output UV power	Pout	mW	0.5			IF=20 mA
Peak wavelength	λp	nm	-10 nm	specified	+10 nm	IF=20 mA
Spectrum half width	HW	nm	12	20	30	IF=20 mA





Parameter	Unit	Max rated Value	Ambient Temp
Power dissipation, DC	mW	150	25 °C
Forward current, DC	mA	30	25 °C
Pulse forward current	mA	200	25 °C
Reverse voltage	V	6	25 °C
Storage temperature		- 30 ~ + 100 °C	



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